## DESCRIPTION

The 2505 512-bit and the 2512 1024-bit recirculating dynamic shift registers consist of enhancement mode p-channel MOS devices integrated on a single monolithic chip. Internal recirculation logic plus write and read controls, together with 2 chip select controls are included on the chip.

## BLOCK DIAGRAM



## PIN CONFIGURATION



## ABSOLUTE MAXIMUM RATINGS 1



DC ELECTRICAL CHARACTERISTICS $T_{A}=0^{\circ} \mathrm{C}$ to $70^{\circ} \mathrm{C}, \mathrm{V}_{C C}=5 \mathrm{~V} \pm 5 \%, \mathrm{~V}_{D D}=-5 \mathrm{~V} \pm 5 \%$ unless otherwise specified.

|  | PARAMETER | TEST CONDITIONS | 2505 |  |  | 2512 |  |  | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Min | Typ | Max | Min | Typ | Max |  |
|  | Input voltage ${ }^{3}$ |  |  |  |  |  |  |  | V |
| VIL | Low |  | -5.0 |  | 0.6 | -5.0 |  | 0.6 |  |
| $\mathrm{V}_{1 \text { H }}$ | High |  | 3.4 |  | 5.3 | 3.4 |  | 5.3 |  |
| VILC | Clock low |  | -12.0 |  | -10.0 | -12.0 |  | -10.0 |  |
| VIHC | Clock high |  | 4.0 |  | 5.3 | 4.0 |  | 5.3 |  |
|  | Output voltage |  |  |  |  |  |  |  | V |
| Vol | Low | $\mathrm{R}_{\mathrm{L}}=3.0 \mathrm{~K}, 1 \mathrm{TTL}$ load $(\mathrm{l}=1.6 \mathrm{~mA}) 4$ |  | -1.0 |  |  | -1.0 |  |  |
| Voh1 | High, driving 1 TTL load | $R_{L}=3.0 \mathrm{~K}, 1 \mathrm{TTL}$ load ( $\mathrm{K}=100 \mu \mathrm{~A}$ ) | 2.4 | 3.5 |  | 2.4 | 3.5 |  |  |
| VOH2 | High, driving MOS | $\mathrm{R}_{\mathrm{L}}=5.6 \mathrm{~K}, \mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}$ | 3.6 | 4.0 |  | 3.6 | 4.0 |  |  |
| ILI | Input load current | $\mathrm{V}_{\text {IN }}=5.5 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  | 10 | 500 |  | 10 | 500 | nA |
|  | Leakage current | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  |  |  |  |  |  | nA |
| ILO | Output | $V_{\phi_{1}}=V_{\phi_{2}}=-12 \mathrm{~V}, \mathrm{~V}_{\text {DD }}=-5 \mathrm{~V}, \mathrm{~V}_{\text {OUT }}=-5.5 \mathrm{~V}$ |  | 10 | 1000 |  | 10 | 1000 |  |
| ILC | Clock | $\mathrm{V}_{\text {ILC }}=-12 \mathrm{~V}$ |  | 10 | 1000 |  | 10 | 1000 |  |
| IDD | Supply current | Continuous operation, $\phi \mathrm{pW}=150 \mathrm{~ns}, 1 \mathrm{MHz}$, $V_{I L C}=-12 \mathrm{~V}, T_{A}=25^{\circ} \mathrm{C}, \mathrm{V}_{D D}=-5.5 \mathrm{~V}$ |  | 15 | 25 |  | 25 | 35 | mA |
|  | Capacitance | $1 \mathrm{MHz}, \mathrm{V}_{\text {AC }}=25 \mathrm{mV}$ p-p |  |  |  |  |  |  | pF |
| $\mathrm{CIN}^{\text {N }}$ | Input | $\mathrm{V}_{1}=\mathrm{V}_{\mathrm{cc}}$ |  |  |  |  |  |  |  |
| Cout | Output | $V_{0}=V_{C C}$ |  |  | 5 |  |  | 5 |  |
| $\mathrm{C}_{\text {¢ }}$ | Clock |  |  |  | 50 |  |  | 100 |  |

AC ELECTRICAL CHARACTERISTICS $T_{A}=25^{\circ} \mathrm{C}, \mathrm{V}_{\mathrm{CC}}=5 \mathrm{~V} 3, \mathrm{~V}_{\mathrm{DD}}=-5 \mathrm{~V} \pm 5 \%, \mathrm{~V}_{\mathrm{ILC}}=-11 \mathrm{~V}$

| PARAMETER | TO | FROM | TEST CONDITIONS | LIMITS |  |  | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min | Typ | Max |  |
| Freq. Clock data rep rate <br> $t_{\phi P W}$ Clock pulse width <br> $t_{\phi D}$ Clock pulse delay <br> $t_{r}, t_{F}$ Clock pulse transition |  |  | $\mathrm{W}=\mathrm{R}=\mathrm{VCC}$ | $\begin{gathered} .0005 \\ 180 \\ 10 \end{gathered}$ | 3 | $2.5$ <br> 1 | $\begin{gathered} \mathrm{MHz} \\ \mathrm{~ns} \\ \mathrm{~ns} \\ \mu \mathrm{~s} \end{gathered}$ |
|  Setup and hold time <br> tow Setup time <br> to Hold time | Input clock Data in | Data in Input clock |  | $\begin{gathered} 150 \\ 10 \end{gathered}$ |  |  | ns |
| $\mathrm{t}_{A_{+}, \mathrm{t}_{\text {- }} \text { - Delay time }}$ | Data out | Clock |  |  |  | 100 | ns |
| Clock to read or chip select or write timing $\begin{aligned} & \mathrm{t}_{\mathrm{R}-, \mathrm{tcs}-, \mathrm{t}_{\mathrm{w}}} \\ & \mathrm{t}_{\mathrm{R}-,}, \mathrm{tcs}^{2}, \mathrm{~T}_{\mathrm{w}}+ \end{aligned}$ |  |  |  | 0 0 |  |  | ns |

## NOTES

1. Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied.
2. For operating at elevated temperatures the device must be derated based on a $+150^{\circ} \mathrm{C}$ maximum junction temperature and a thermal resistance of $150^{\circ} \mathrm{C} / \mathrm{W}$ junction to ambient.
3. Guaranteed input levels are stated for worst case conditions including a $\pm 5 \%$ variation in Vcc and a temperature variation of $0^{\circ} \mathrm{C}$ to $+70^{\circ} \mathrm{C}$. Actual input requirements with respect to $\mathrm{V}_{\mathrm{CC}}$ are $\mathrm{V}_{\mathbb{H}}=\mathrm{V}_{\mathrm{CC}}-$ 1.85 V and $\mathrm{V}_{\mathrm{IL}}=\mathrm{Vcc}-4.15 \mathrm{~V}$.
4. $V_{O L}$ is a function of the input characteristics of the driven TTL/DTL gate lo. and VCLAMP and the value of the pull-down resistor ( $R_{L}$ ).
5. All inputs are protected against static charge.
6. Parameters are valid over operating temperature range unless otherwise specified.
7. All voltage measurements are referenced to ground.
8. Manufacturer reserves the right to make design and process changes and improvements.
9. Typical values are at $+25^{\circ} \mathrm{C}$ and typical supply voltage.

## TIMING DIAGRAM



